

Process Development & Forensics of SOI Nanoscale Membranes

Ryan Stewart | Tom Harris | John Nogan | Don Bethke

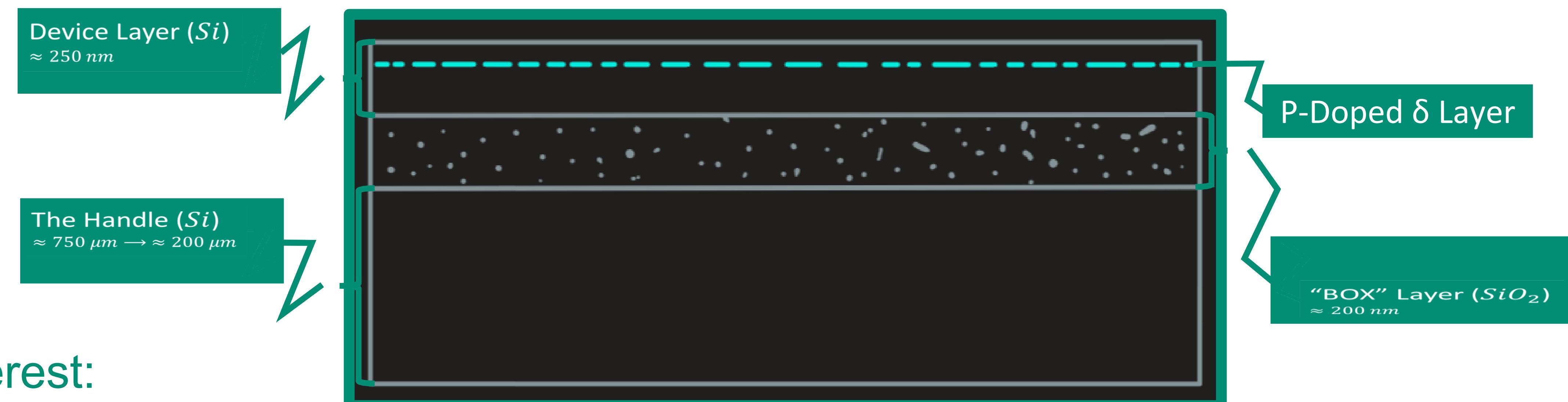
Introduction & Motivation

Motivation: Understand and measure thermopower in a P-doped quantum material.



Michelle Simmons: Queen of Quantum Computers

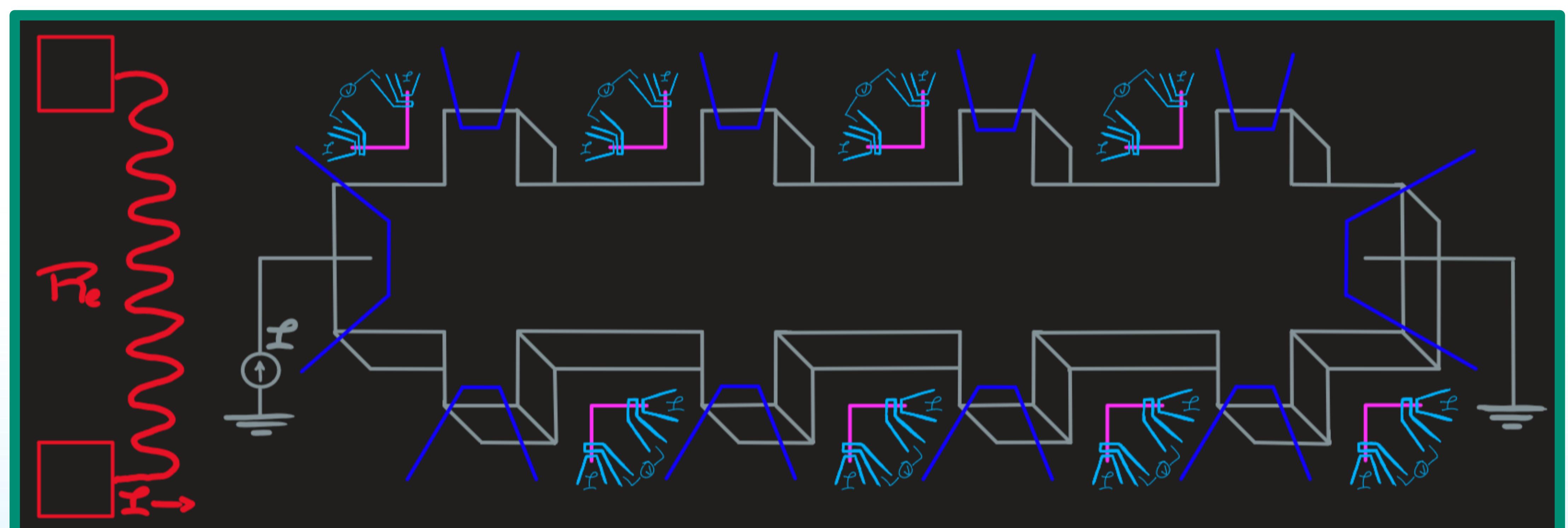
SNL: Shashank Misra & Ezra Bussman



Measurements of Interest:

- Carrier Type, Density, and Mobility
- Seebeck Coefficient

Hall Bar with a Heater and a ton of Thermometers



The Seebeck Coefficient

$$S = \frac{\partial V}{\partial T} = - \frac{\Delta V}{\Delta T}$$



Introduction & Motivation Continued

Why SOI?

Thermal Ohm's Law

$$\Delta T = R_{th} \dot{Q}$$

$$\text{Where } R_{th} = \frac{L}{k_A} = \frac{L}{k_{WT}}$$

$$\Rightarrow R_{th, Si} = \frac{10\mu m}{(10 \frac{W}{m \cdot K})(500\mu m)(10\mu m)} = 200 \frac{K}{W}$$

Therefore, to achieve a temperature difference of 1 K we will need

$$\Rightarrow \dot{Q}_{Si} = \frac{\Delta T}{R_{th, Si}} = \frac{1K}{200 \frac{K}{W}} = 5mW$$

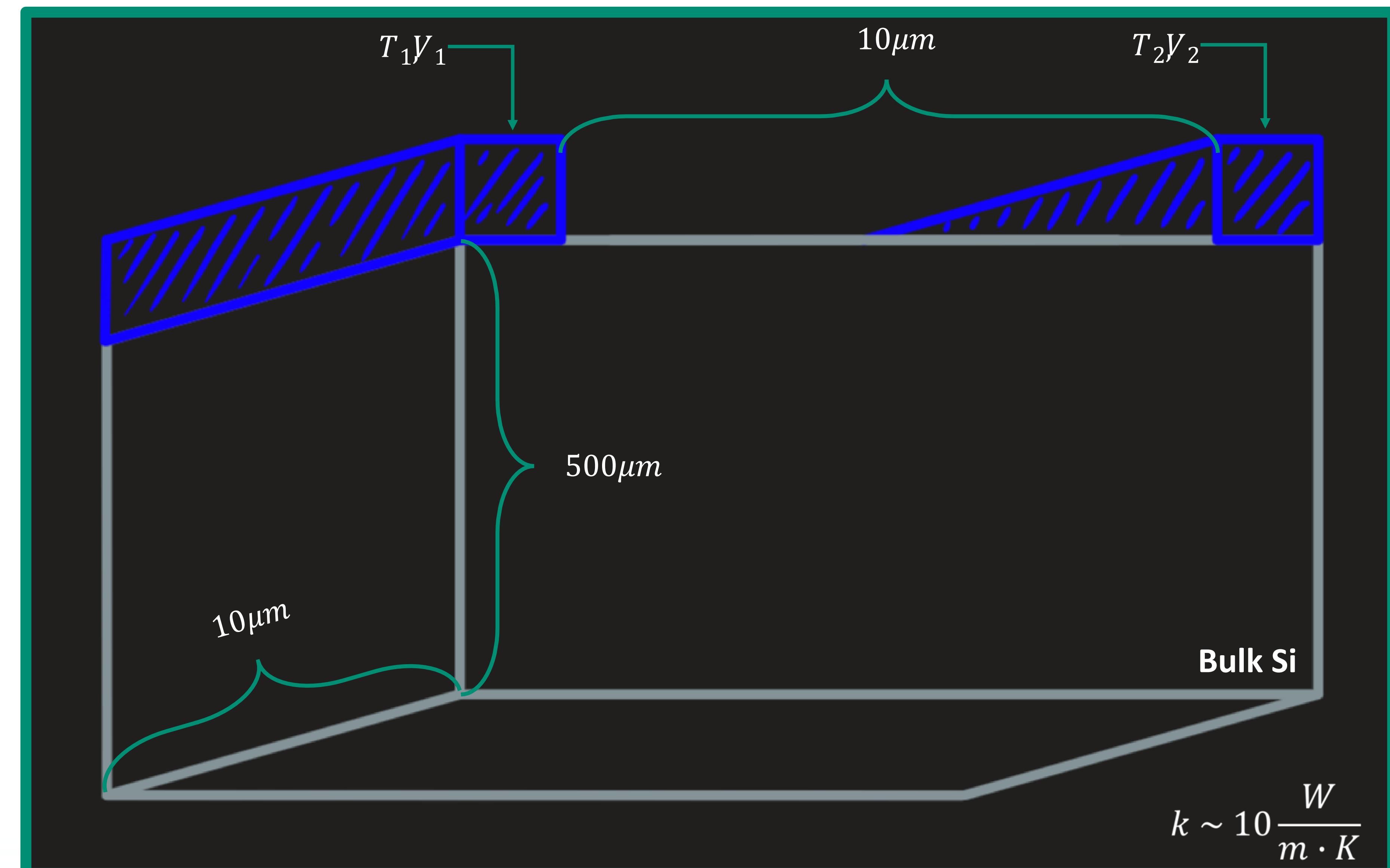
Cryogenic System Power Output Limits:

- ➔ 3He can produce $40\mu W$ of cooling power
- ➔ Dilution Fridge can produce between $200\mu W$ and $400\mu W$ of cooling power

& if we compare

$$t_{Si} = 500\mu m \text{ vs. } t_{SOI} = 250nm$$

Nominal Dimensions for Optical Lithography Patterning

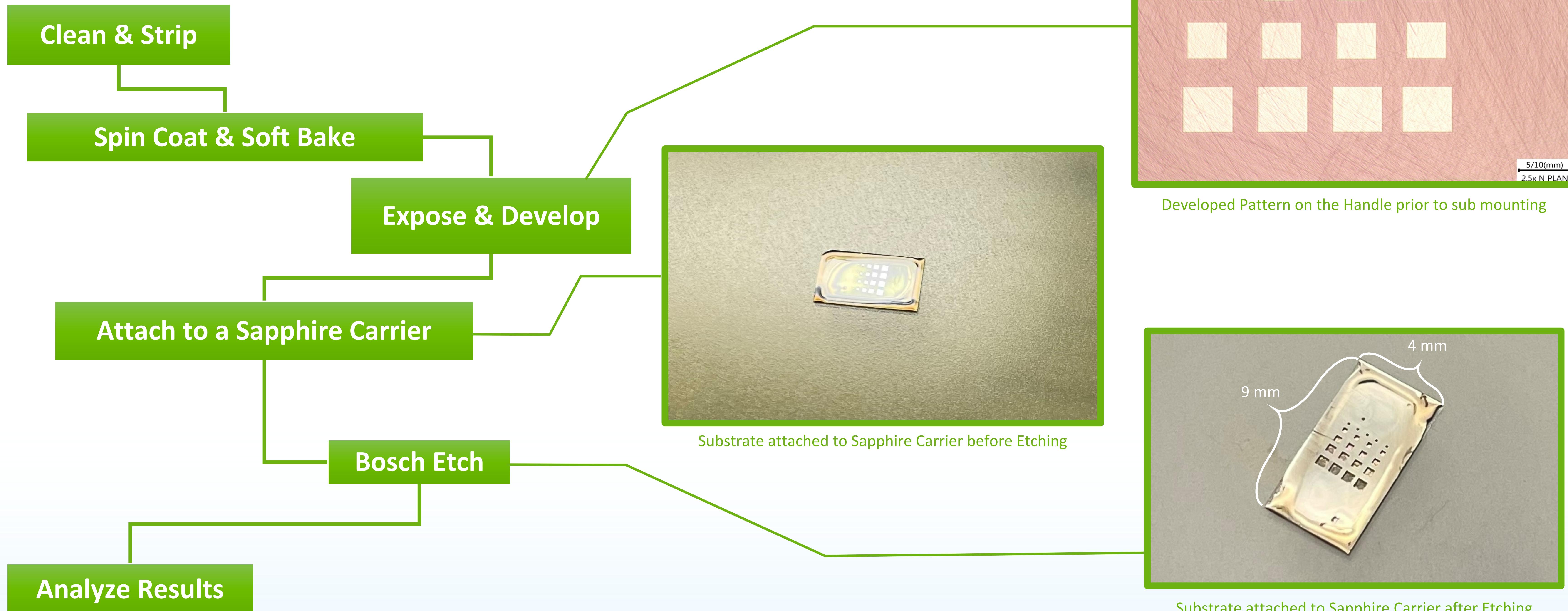


$$\Rightarrow \dot{Q}_{SOI} = 2.5\mu W \text{ (2000 times less!!)}$$

Approach

QUESTION: How big of a membrane can we make?

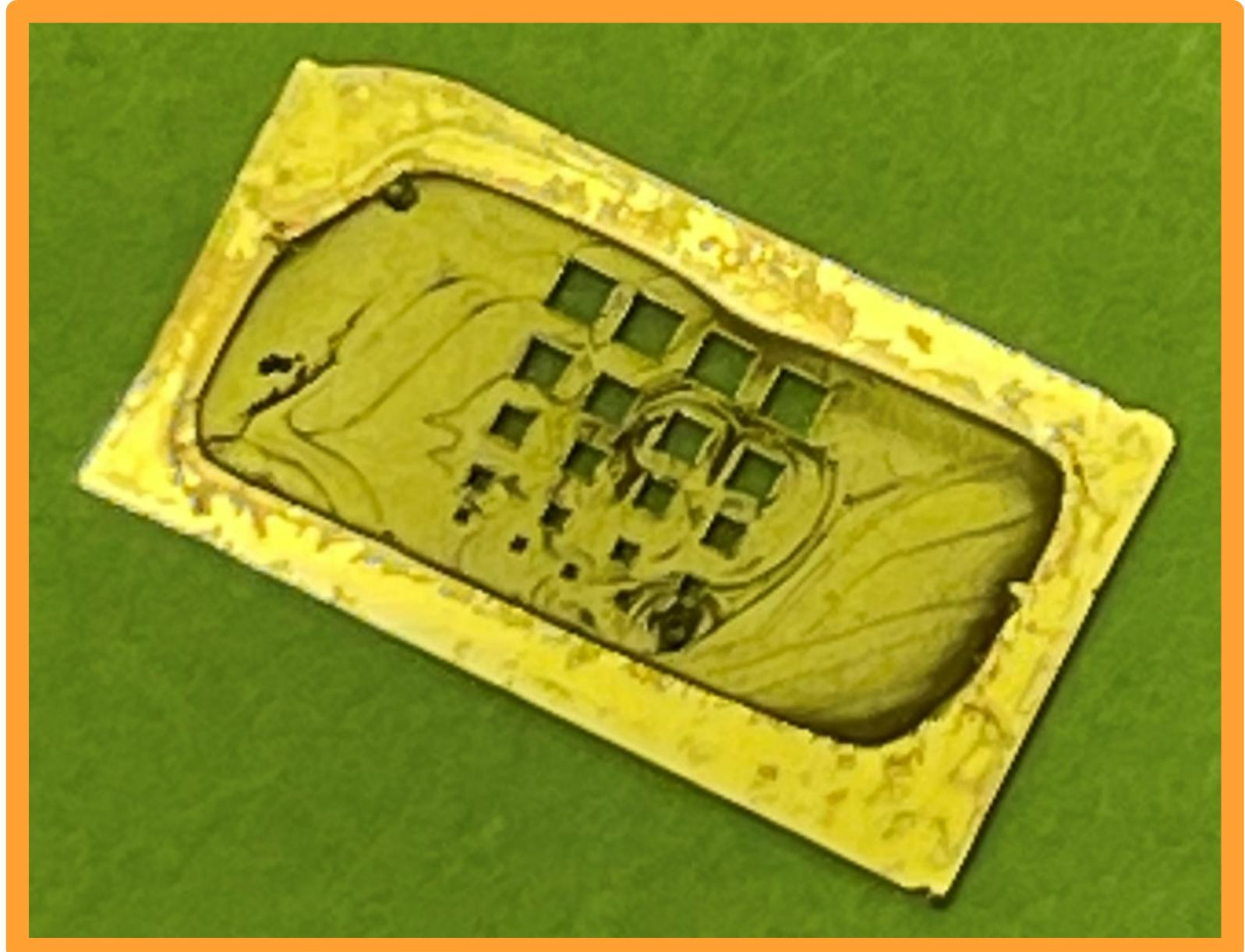
My Process Flow





Challenges

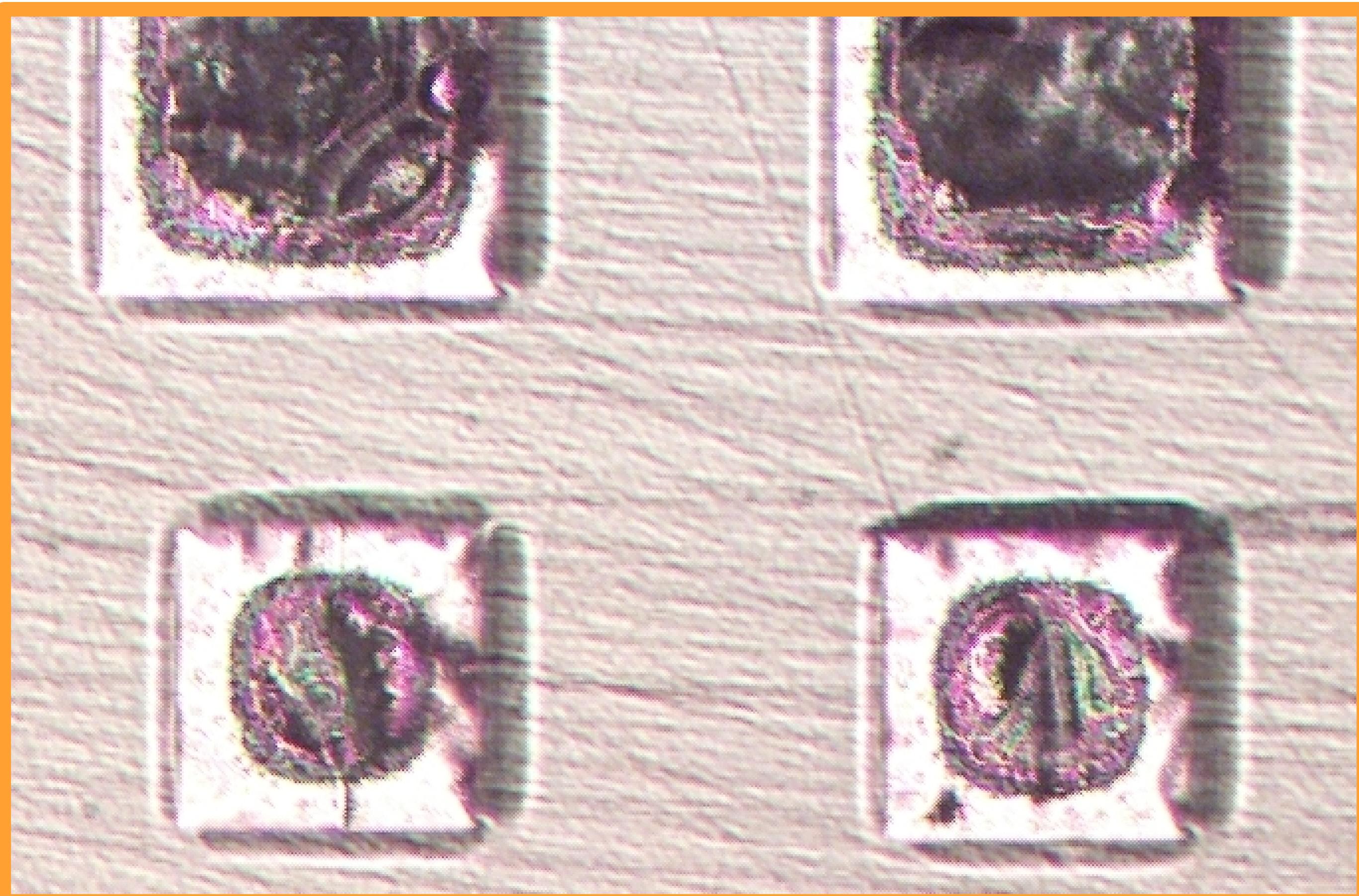
1.) Depleted Resist & Blown Out Membranes



Our Response:

- 1) Thicker Resist & Si Etch Rate Test
- 2) Bosch Etch with a 2 Phase Process
- 3) Add Protective Coating to the Device Layer, such as ProTEK B3

2.) Directional Control Issue



3.) Mechanical Failure Evidence

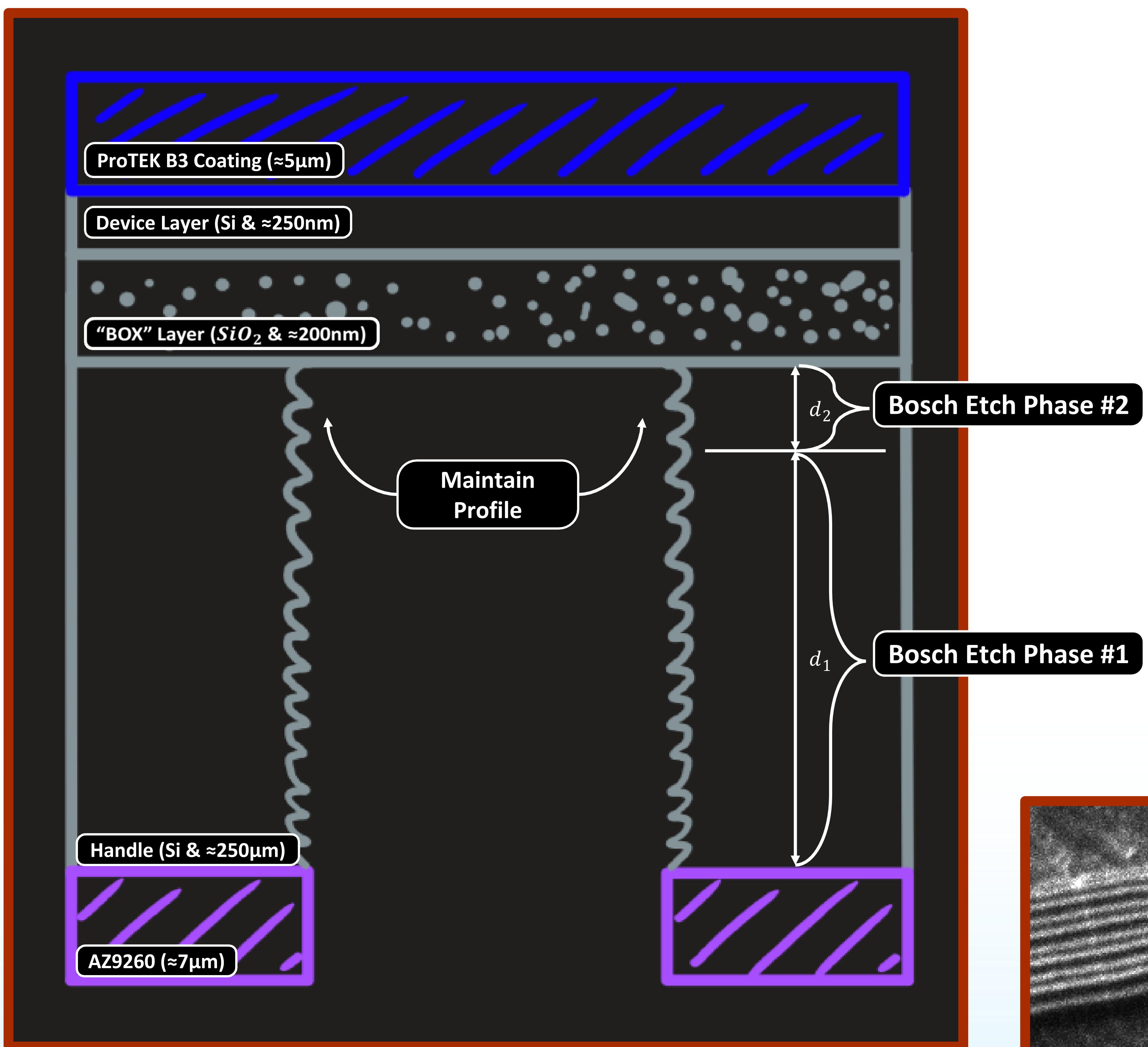


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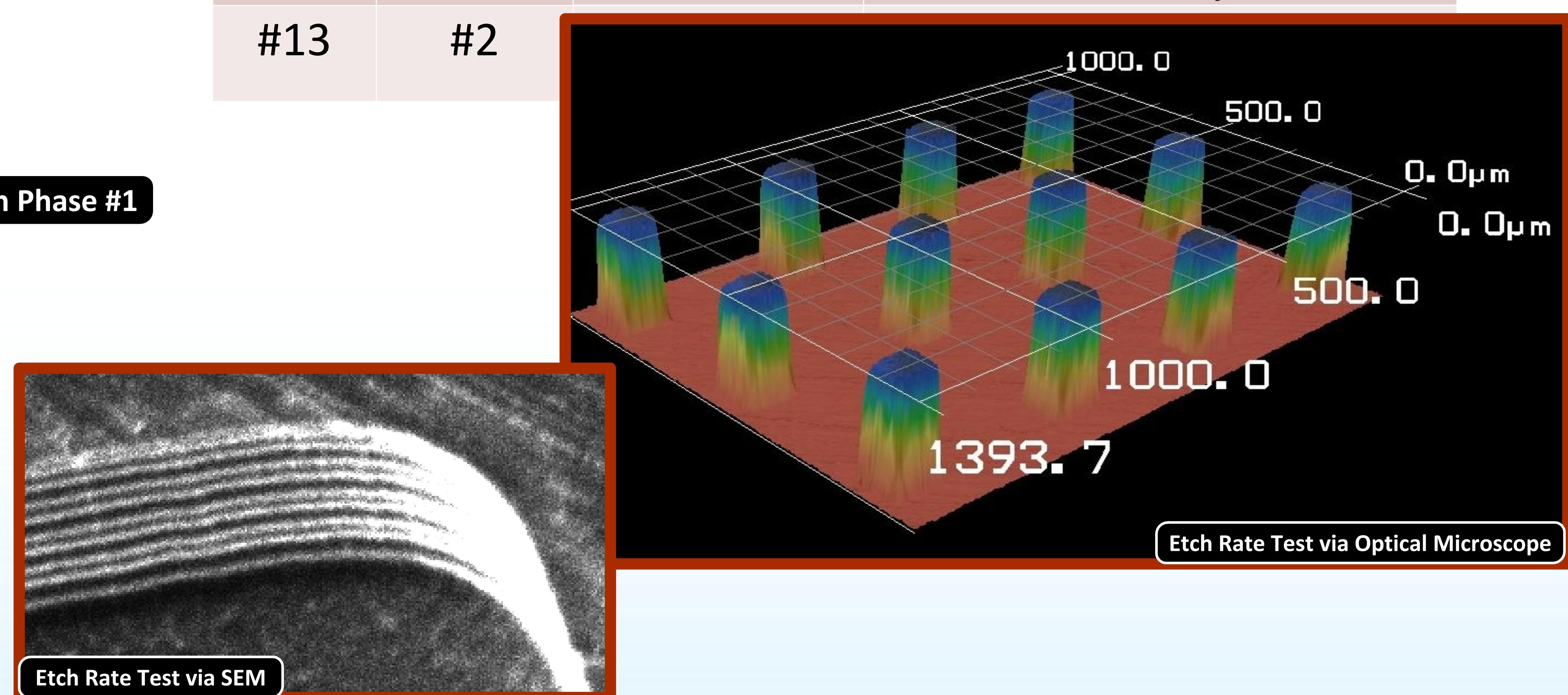
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Results

Quantified Etch Rates & Developed Lithography and Etching Recipes

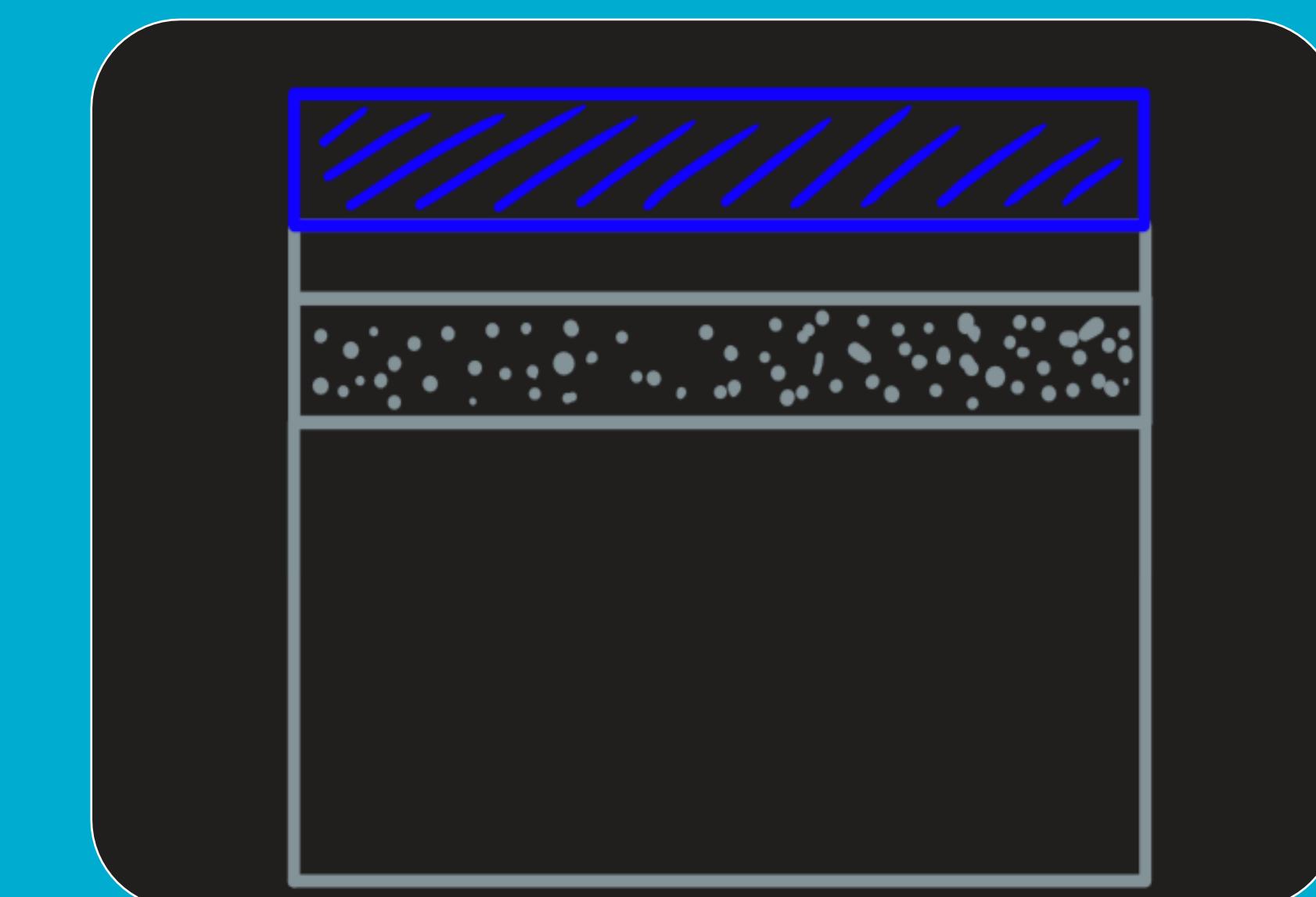


Test	Phase	Material	Etch Rate
#2	#1	Si	$\sim 0.604 \frac{\mu\text{m}}{\text{cycle}}$
#6	#1	SiO ₂	$\sim 4.3 \frac{\text{nm}}{\text{cycle}}$
#6	#1	AZ9260	$\sim 15 \frac{\text{nm}}{\text{cycle}}$
#7	#1	Si	$\sim 0.623 \frac{\mu\text{m}}{\text{cycle}}$
#11	#2	Si	$\sim 0.762 \frac{\mu\text{m}}{\text{cycle}}$
#13	#2		





Ongoing & Future Work



Using a Polymer as Structural Support

→ Spin coat the device layer before spin resist on the handle.

→ For Example, a ProTEK B3 Coating is used to protect delicate front-side circuitry during back-side micromachining.



Use an SOI with a thicker BOX and Device

→ Pro: Increases the structural integrity

→ Con: New process needed for embedding Phosphine